



PATENT

CASE NAME/No.: SP02-152

THE UNITED STATES PATENT AND TRADEMARK OFFICE

Inventor: Guillermo Guzman et al.

Serial No: 10/668873

Art Group Unit: 2826

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Examiner: Thomas L. Dickey

Title: UNDER LAYER FOR POLYSILICON TFT

RESPONSE

Commissioner for Patents  
Alexandria, VA 22313-1450

**RESPONSE TO EXAMINER'S RESTRICTION REQUIREMENT**

In the Office Action dated June 16, 2004, designated as Paper No. 200406 in the above-captioned application, the Examiner issued a Restriction Requirement identifying the following groups of claims as being drawn to potentially distinct inventions:

- Group I. Claims 15 - 18, drawn to a method, classified in class 438, subclass 958; and
- Group II. Claims 1 - 14 and 19, drawn to a device, classified in class 257, subclass 636.

A provisional election to Group II, claims 1-14 and 19 is made without traverse.

As a formality, Applicants hereby cancel claims 15-18, without prejudice.

**IN THE CLAIMS**

1. (Original) A semiconductor device comprising:

- a substrate suitable for use in electronic and integrated circuits;
- a layer of refractory polycrystalline material formed on at least a portion of the substrate;
- and
- a layer of polycrystalline silicon formed on the refractory layer.

2. (Original) A semiconductor device according to claim 1 wherein said device is a thin film transistor (TFT) suitable for applications selected from the group consisting of liquid crystal displays (LCDs) and light emitting diodes (LEDs).

3. (Original) A semiconductor device according to claim 1 wherein the substrate is glass, glass-ceramic, ceramic, metal or plastic.